Oral presentation | 13 Semiconductors | 13.7 Compound and power electron devices and process technology

[20a-E301-1~12] 13.7 Compound and power electron devices and process technology

Kenji Shiojima (Univ. of Fukui)
Fri. Sep 20, 2019 9:00 AM - 12:15 PM  E301 (E301)
△: Presentation by Applicant for JSAP Young Scientists Presentation Award
▲: English Presentation
▼: Both of Above
No Mark: None of Above

9:00 AM - 9:15 AM

[20a-E301-1][INVITED] Temperature dependence of barrier height in Ni/n-GaN Schottky barrier diode
OTakuya Maeda¹, Masaya Okada², Masaki Ueno², Yoshiyuki Yamamoto², Tsunenobu Kimoto¹, Masahiro Horita³, Jun Suda² (1.Kyoto Univ., 2.Sumitomo Electric Industries, 3.Nagoya Univ.)
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